

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

### LISTING OF THE CLAIMS:

Claims 1-30 (Cancelled)

31. (currently amended) A method of manufacturing a semiconductor device, comprising the steps of:

providing a wiring substrate including a main surface, an insulating film formed on the main surface, and a plurality of electrodes formed on the main surface, a surface of the plurality of electrodes being exposed from the insulating film;

providing a semiconductor chip having a main surface and a back surface, a plurality of semiconductor elements and a plurality of electrodes being formed on the main surface of the semiconductor chip;

fixing the semiconductor chip to the insulating film through a pasty adhesive;

after the fixing step, connecting one end of a plurality of conductive wires to the plurality of electrodes on the main surface of the wiring substrate;

covering the semiconductor chip, the main surface of the wiring substrate and the plurality of conductive wires with a sealing resin;

wherein previous to the fixing step, a groove is formed in the insulating film so as to expose the main surface of the wiring substrate between the plurality of electrodes

formed on the main surface of the wiring substrate and the semiconductor chip, and the fixing step is performed so as to allow a protruding portion of the pasty adhesive flowing out to the outside of the semiconductor chip to stay in the groove so as not to reach the plurality of electrodes formed on the main surface of the wiring substrate, and

wherein the pasty adhesive is formed on a peripheral surface of the semiconductor chip as a slope surface by a raised portion of the pasty adhesive.

32. (currently amended) A ~~semiconductor device~~ method according to claim 31, wherein the plurality of conductive wires are electrically connected between the plurality of electrodes on the main surface of the wiring substrate and the plurality of electrodes on the main surface of the semiconductor chip.

33. (new) A method according to claim 31, wherein the groove extends to a region below the semiconductor chip.

34. (new) A method according to claim 31, wherein the step of fixing the semiconductor chip comprises:

holding the semiconductor chip with a bonding tool;  
bringing the held chip into proximity with the insulating film; and

fixing the semiconductor chip to the insulating film through the pasty adhesive.

35. (new) A method according to claim 31, wherein the semiconductor chip is located away from the groove.

36. (new) A method of manufacturing a semiconductor device, comprising the steps of:

providing a wiring substrate including a main surface, an insulating film formed on the main surface, and a plurality of electrodes formed on the main surface, a surface of the plurality of electrodes being exposed from the insulating film, the plurality of electrodes being provided for connection with a plurality of conductive wires;

providing a semiconductor chip having a main surface and a back surface, a plurality of semiconductor elements and a plurality of electrodes formed on the main surface;

fixing the semiconductor chip to the insulating film through a pasty adhesive;

after the step of fixing, connecting one end of the plurality of conductive wires to the plurality of electrodes on the main surface of the wiring substrate; and

covering the semiconductor chip, the main surface of the wiring substrate and the plurality of the conductive wires with a sealing resin;

wherein previous to the fixing step, a groove is formed in the insulating film so as to expose the main surface of the wiring substrate between the plurality of electrodes formed on the main surface of the wiring substrate and the semiconductor chip, and the fixing step is performed so as

to allow a protruding portion of the pasty adhesive flowing out to the outside of the semiconductor chip to stay in the groove so as not to reach the plurality of electrodes formed on the main surface of the wiring substrate,

wherein the pasty adhesive is formed on a peripheral surface of the semiconductor chip as a slope surface by a raised portion of the pasty adhesive, and

wherein the semiconductor chip is located away from the groove.